NUP4301MR6T1

Low Capacitance Diode Array for ESD Protection in Four Data Lines

NUP4301MR6T1 is a MicroIntegration™ device designed to provide protection for sensitive components from possible harmful electrical transients; for example, ESD (electrostatic discharge).

Features

- Low Capacitance (1.5 pf Maximum Between I/O Lines)
- Single Package Integration Design
- Provides ESD Protection for JEDEC Standards JESD22
  - Machine Model = Class C
  - Human Body Model = Class 3B
- Protection for IEC61000−4−2 (Level 4)
  - 8.0 kV (Contact)
  - 15 kV (Air)
- Ensures Data Line Speed and Integrity
- Fewer Components and Less Board Space
- Direct the Transient to Either Positive Side or to the Ground
- Pb−Free Package is Available

Applications

- USB 1.1 and 2.0 Data Line Protection
- T1/E1 Secondary IC Protection
- T3/E3 Secondary IC Protection
- HDSL, IDSL Secondary IC Protection
- Video Line Protection
- Microcontroller Input Protection
- Base Stations
- I^2C Bus Protection

MAXIMUM RATINGS (Each Diode) (T_J = 25°C unless otherwise noted)

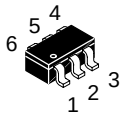
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non−Repetitive Peak Forward Current t = 1.0 μs t = 1.0 ms t = 1.0 S	I_{FSM}	 2.0 1.0 0.5	A

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR−5 = 1.0 × 0.75 × 0.062 in.

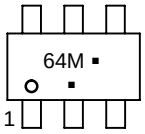
ON Semiconductor®

http://onsemi.com



TSOP−6
CASE 318F
PLASTIC

MARKING DIAGRAM

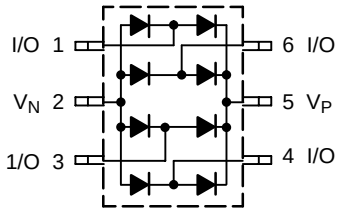


64 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location.

*Date Code orientation may vary depending upon manufacturing location.

PIN CONFIGURATION AND SCHEMATIC



ORDERING INFORMATION

Device	Package	Shipping†
NUP4301MR6T1	TSOP−6	3000/Tape & Reel
NUP4301MR6T1G	TSOP−6 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Lead Solder Temperature, Maximum 10 Seconds Duration	T_L	260	°C
Junction Temperature	T_J	−40 to +85	°C
Storage Temperature	T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Reverse Breakdown Voltage ($I_{(BR)}$ = 100 μA)	$V_{(BR)}$	70	−	−	Vdc
Reverse Voltage Leakage Current (V_R = 70 Vdc) (V_R = 25 Vdc, T_J = 150°C) (V_R = 70 Vdc, T_J = 150°C)	I_R	− − −	− − −	2.5 30 50	μAdc
Capacitance (between I/O pins) (V_R = 0 V, f = 1.0 MHz)	C_D	−	0.8	1.5	pF
Capacitance (between I/O pin and ground) (V_R = 0 V, f = 1.0 MHz)	C_D	−	1.6	3	pF
Forward Voltage (I_F = 1.0 mAdc) (I_F = 10 mAdc) (I_F = 50 mAdc) (I_F = 150 mAdc)	V_F	− − − −	− − − −	715 855 1000 1250	mV_{dc}

2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

Curves Applicable to Each Cathode

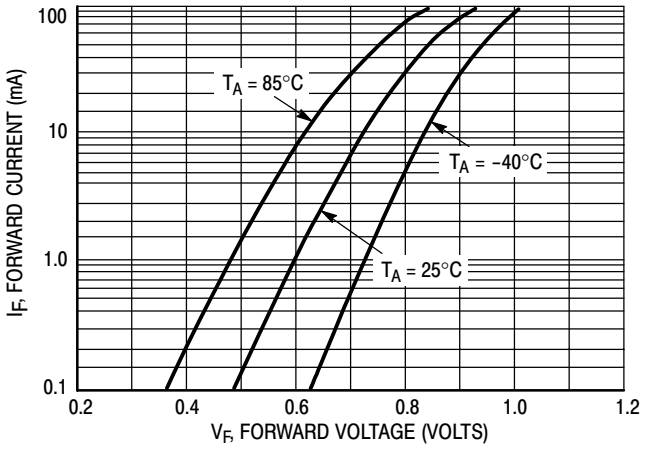


Figure 1. Forward Voltage

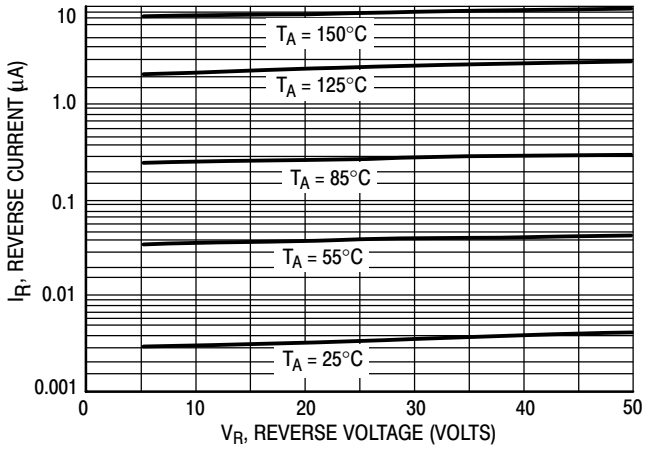


Figure 2. Leakage Current

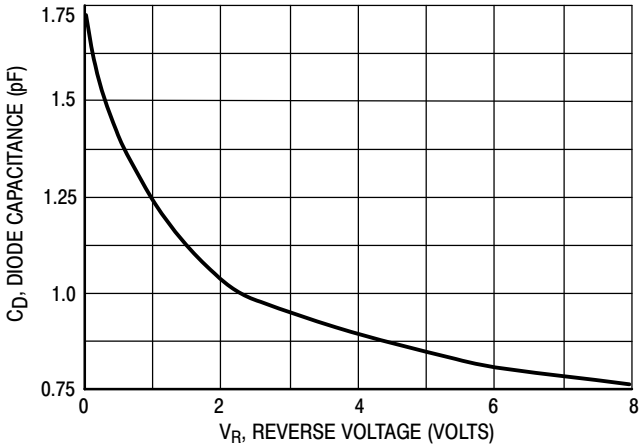
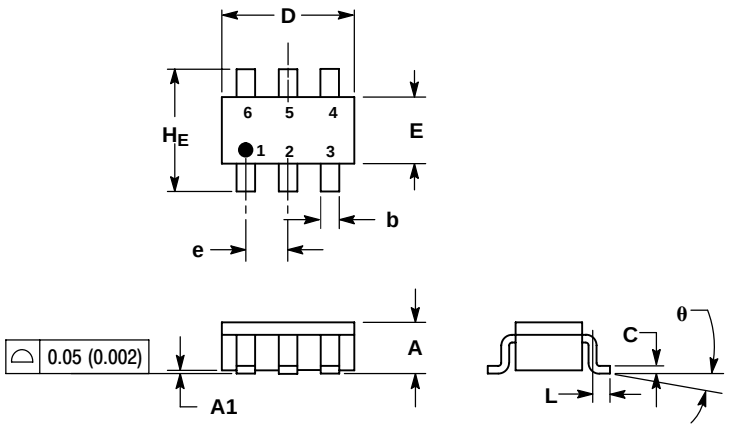


Figure 3. Capacitance

PACKAGE DIMENSIONS

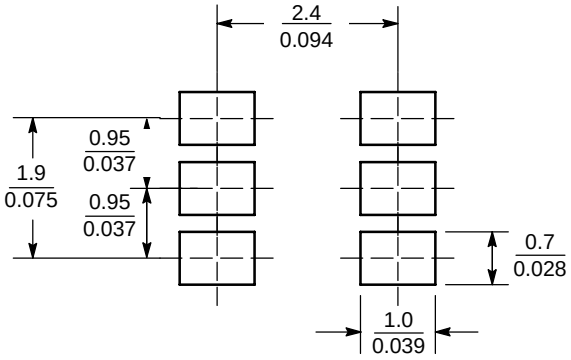
TSOP−6
CASE 318F−05
ISSUE L



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F−01, −02, −03 OBSOLETE. NEW STANDARD 318F−04.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	–	10°	0°	–	10°

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.